

AMENDMENTS TO THE CLAIMS

Please amend Claim 7, 9, and 10 to read as follows:

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7. (Currently Amended) A semiconductor device comprising a substrate ~~and formed thereon an~~ single-crystal silicon active layer used for photoelectric conversion and having a ~~the surface (111)-plane; the active layer being used in photoelectric conversion;~~ where as its surface, wherein an angle formed by any arbitrary two cutting lines contained in the surface and not coming into coincidence is represented by θ , and θ satisfies the expression the active layer has a cutting angle of $|\cos\theta| = \frac{1}{2}$ or $3^{1/2}/2$.

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9. (Currently Amended) The semiconductor device according to Claim 7, wherein ~~the~~ any deviation of said surface from said ~~the strict~~ (111) plane is within an angle equal to 24/60ths of a degree ($0^{\circ}24'$).

10. (Currently Amended) A photoelectric conversion element comprising an anti-reflection layer, ~~semiconductor~~ silicon layers, and an electrode, provided from ~~the~~ a light incident side,

wherein all of the silicon layers are ~~epitaxial~~ single-crystal silicon layers, and wherein the silicon layers comprise an n^{+} layer, and a p^{-} layer of about 30 μm thickness, provided from the light incident side, wherein a surface of the silicon layers has a (111) plane, and wherein any deviation of said surface from said (111) plane is within an angle equal to 24/60ths of a degree ($0^{\circ}24'$).